(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
7 June 2007 (07.06.2007)

PCT

(10) International Publication Number
WO 2007/064501 A1

(51) International Patent Classification:
H01L 21/768 (2006.01)

(21) International Application Number:
PCT/US2006/044719

(22) International Filing Date:
17 November 2006 (17.11.2006)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/291,411 30 November 2005 (30.11.2005) US

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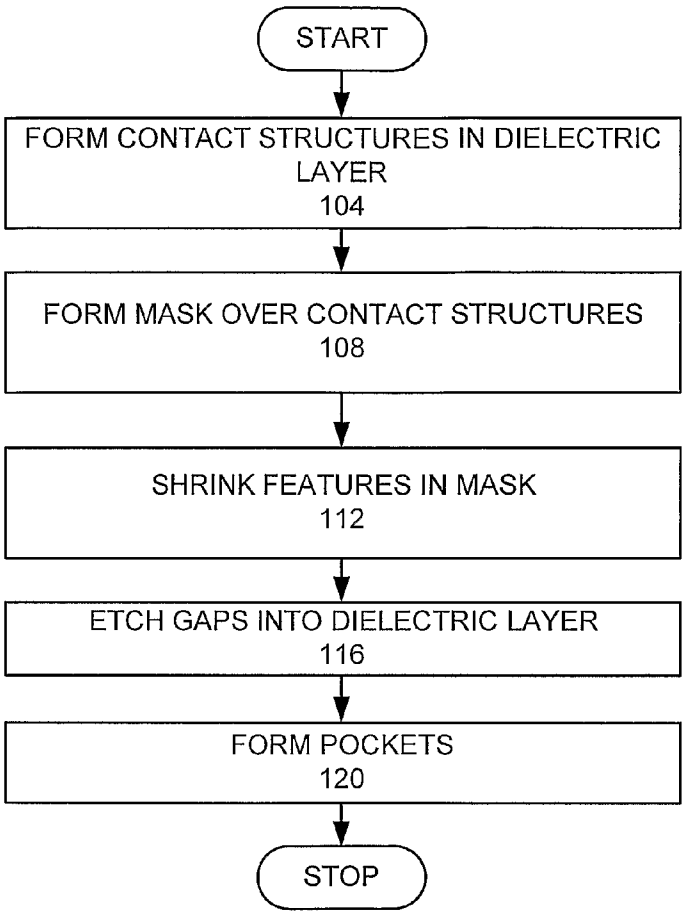
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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,

[Continued on next page]

(54) Title: DEVICE WITH GAPS FOR CAPACITANCE REDUCTION



(57) Abstract: A method for reducing capacitances between semiconductor devices is provided. A plurality of contact structures (210) is formed in a dielectric layer (208) . A mask (212) is formed to cover the contact structures wherein the mask has mask features (214) for exposing parts of the dielectric layer wherein the mask features have widths . The widths of the mask features are shrunk with a sidewall deposition (215) . Gaps (216) are etched into the dielectric layer through the sidewall deposition. The gaps are closed to form pockets (220) in the gaps .

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FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report*

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